

General purpose (dual digital transistors)

UMH7N / IMH7A

●Features

- 1) Includes two DTC143T transistors in a single UMT package.

●Absolute maximum ratings (Ta=25°C)

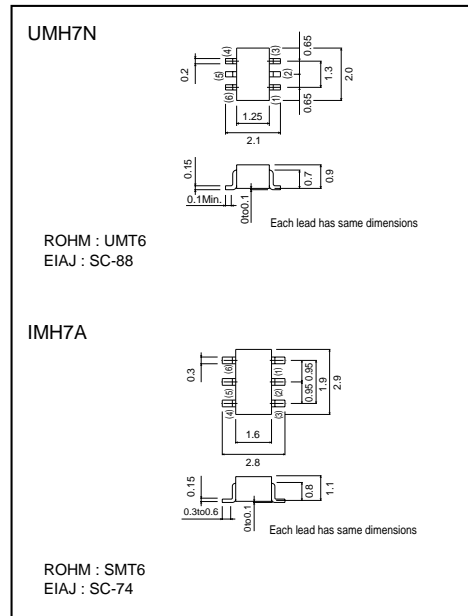
Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CB0}	50	V
Collector-emitter voltage	V _{CE0}	50	V
Emitter-base voltage	V _{EB0}	5	V
Collector current	I _c	100	mA
Collector power dissipation	P _c	150 (TOTAL)	mW *1
		300 (TOTAL)	
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55~+150	°C

*1 120mW per element must not be exceeded.
*2 200mW per element must not be exceeded.

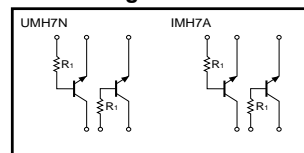
●Package, marking, and Packaging specifications

Part No.	UMH7N	IMH7A
Package	UMT6	SMT6
Marking	H7	H7
Code	TR	T108
Basic ordering unit (pieces)	3000	3000

●External dimensions (Units : mm)



●Circuit diagram



●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CB0}	50	-	-	V	I _c =50μA
Collector-emitter breakdown voltage	BV _{CE0}	50	-	-	V	I _c =1mA
Emitter-base breakdown voltage	BV _{EB0}	5	-	-	V	I _E =50μA
Collector cutoff current	I _{cbo}	-	-	0.5	μA	V _{CE} =50V
Emitter cutoff current	I _{EBO}	-	-	0.5	μA	V _{EB} =4V
DC current transfer ratio	h _{FE}	100	250	600	-	V _{CE} / I _c =5V / 1mA
Collector-emitter saturation voltage	V _{CE(sat)}	-	-	0.3	V	I _c / I _B =5mA / 0.25mA
Input resistance	R _i	3.29	4.7	6.11	kΩ	-